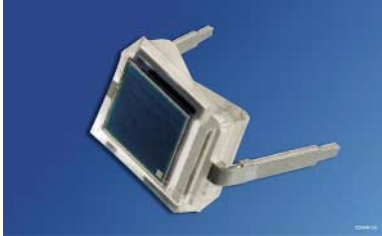
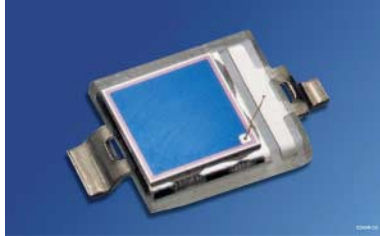


Silizium-PIN-Fotodiode; in SMT und als Reverse Gullwing
Silicon PIN Photodiode; in SMT and as Reverse Gullwing
Lead (Pb) Free Product - RoHS Compliant
BPW 34, BPW 34 S, BPW 34 S (R18R)



BPW 34



BPW 34 S



BPW 34 S (R18R)

Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 400 nm bis 1100 nm
- Kurze Schaltzeit (typ. 20 ns)
- DIL-Plastikbauform mit hoher Packungsdichte
- BPW 34 S/(R18R): geeignet für Vapor-Phase Löten und IR-Reflow Löten

Anwendungen

- Lichtschranken für Gleich- und Wechsellichtbetrieb
- IR-Fernsteuerungen
- Industrieelektronik
- „Messen/Steuern/Regeln“

Features

- Especially suitable for applications from 400 nm to 1100 nm
- Short switching time (typ. 20 ns)
- DIL plastic package with high packing density
- BPW 34 S/(R18R): suitable for vapor-phase and IR-reflow soldering

Applications

- Photointerrupters
- IR remote controls
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code
BPW 34	Q62702P0073
BPW 34 S	Q65110A1209
BPW 34 S (R18R)	Q65110A2701

Grenzwerte
Maximum Ratings

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	° C
Sperrspannung Reverse voltage	V_R	32	V
Verlustleistung, $T_A = 25\text{ °C}$ Total power dissipation	P_{tot}	150	mW

Kennwerte ($T_A = 25\text{ °C}$, Normlicht A, $T = 2856\text{ K}$)
Characteristics ($T_A = 25\text{ °C}$, standard light A, $T = 2856\text{ K}$)

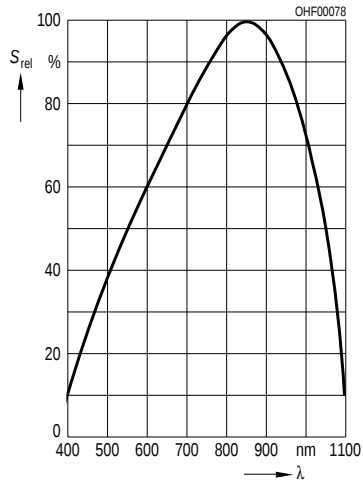
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Fotoempfindlichkeit, $V_R = 5\text{ V}$ Spectral sensitivity	S	80 (≥ 50)	nA/lx
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\text{ max}}$	850	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von S_{max} Spectral range of sensitivity $S = 10\%$ of S_{max}	λ	400 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	A	7.00	mm ²
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	2.65×2.65	mm × mm
Halbwinkel Half angle	φ	± 60	Grad deg.
Dunkelstrom, $V_R = 10\text{ V}$ Dark current	I_R	2 (≤ 30)	nA
Spektrale Fotoempfindlichkeit, $\lambda = 850\text{ nm}$ Spectral sensitivity	S_λ	0.62	A/W
Quantenausbeute, $\lambda = 850\text{ nm}$ Quantum yield	η	0.90	<u>Electrons</u> Photon
Leerlaufspannung, $E_v = 1000\text{ lx}$ Open-circuit voltage	V_O	365 (≥ 300)	mV

Kennwerte ($T_A = 25\text{ °C}$, Normlicht A, $T = 2856\text{ K}$)

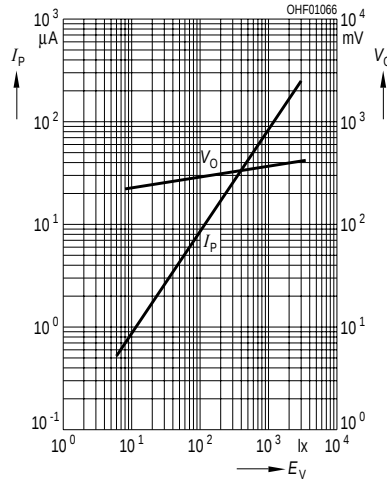
Characteristics ($T_A = 25\text{ °C}$, standard light A, $T = 2856\text{ K}$) (cont'd)

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Kurzschlussstrom, $E_v = 1000\text{ lx}$ Short-circuit current	I_{SC}	80	μA
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent $R_L = 50\text{ }\Omega$; $V_R = 5\text{ V}$; $\lambda = 850\text{ nm}$; $I_p = 800\text{ }\mu\text{A}$	t_r, t_f	20	ns
Durchlassspannung, $I_F = 100\text{ mA}$, $E = 0$ Forward voltage	V_F	1.3	V
Kapazität, $V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0$ Capacitance	C_0	72	pF
Temperaturkoeffizient von V_O Temperature coefficient of V_O	TC_V	- 2.6	mV/K
Temperaturkoeffizient von I_{SC} Temperature coefficient of I_{SC}	TC_I	0.18	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 10\text{ V}$, $\lambda = 850\text{ nm}$	NEP	4.1×10^{-14}	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 10\text{ V}$, $\lambda = 850\text{ nm}$ Detection limit	D^*	6.6×10^{12}	$\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$

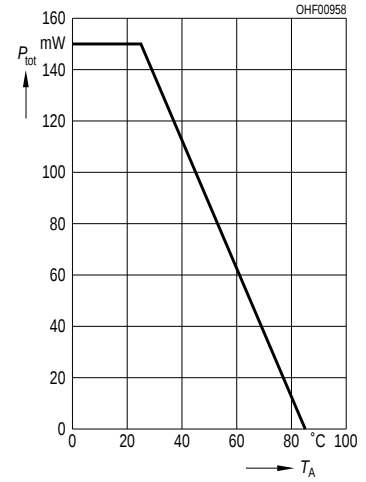
Relative Spectral Sensitivity
 $S_{rel} = f(\lambda)$



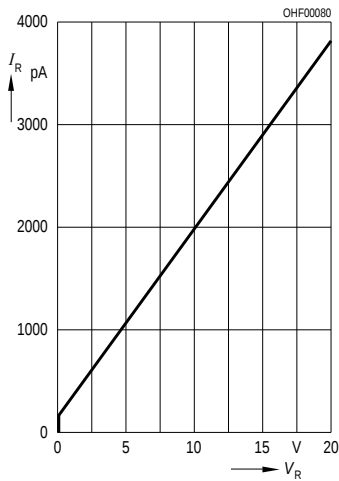
Photocurrent $I_P = f(E_V)$, $V_R = 5$ V
Open-Circuit Voltage $V_O = f(E_V)$



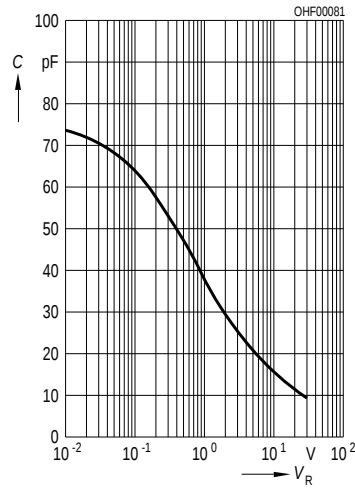
Total Power Dissipation
 $P_{tot} = f(T_A)$



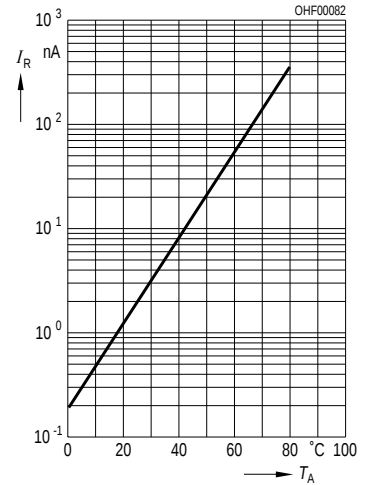
Dark Current
 $I_R = f(V_R), E = 0$



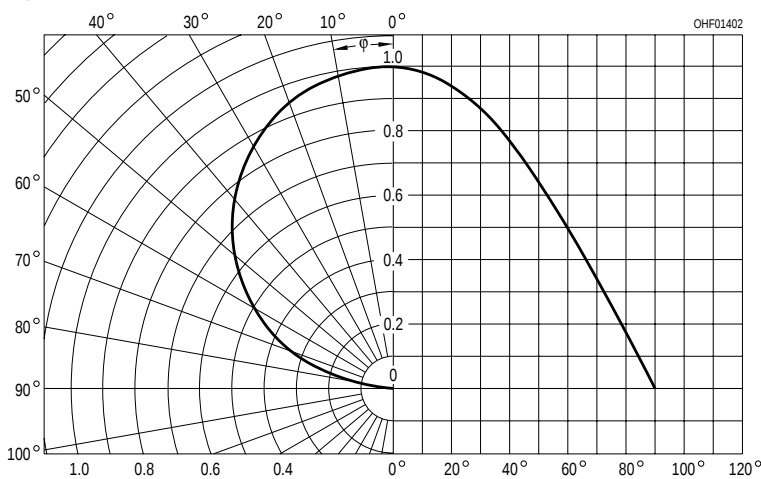
Capacitance
 $C = f(V_R), f = 1$ MHz, $E = 0$



Dark Current
 $I_R = f(T_A), V_R = 10$ V, $E = 0$

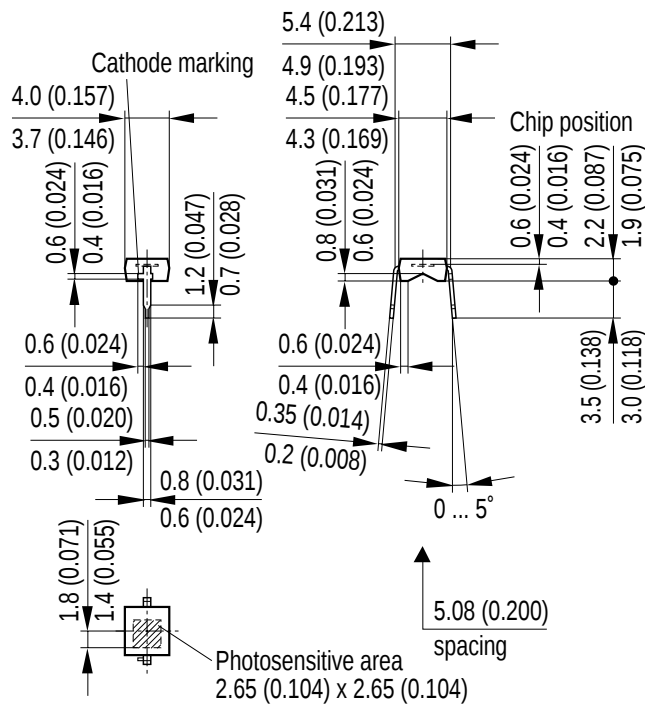


Directional Characteristics
 $S_{rel} = f(\phi)$



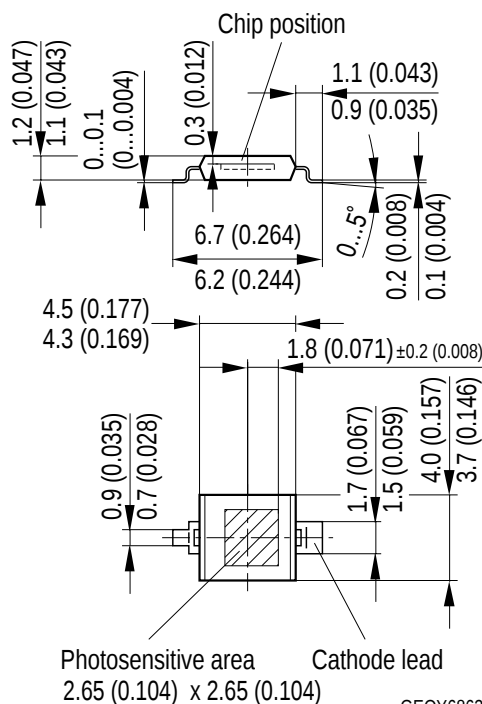
Maßzeichnung
Package Outlines

BPW 34



GEOY6643

BPW 34 S



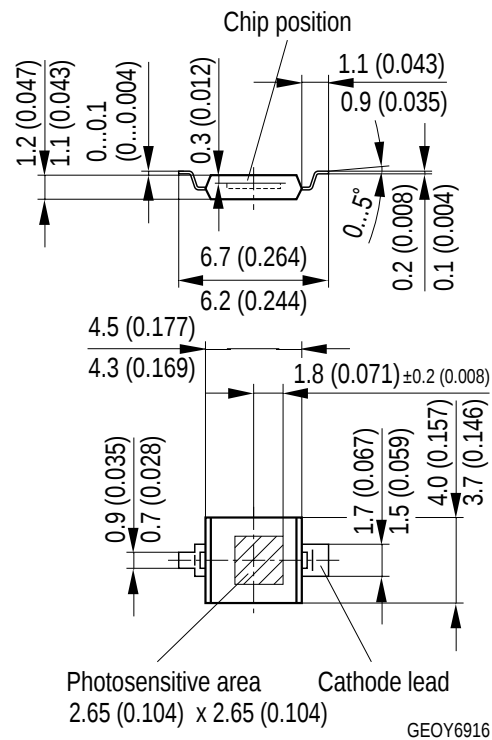
GEOY6863

Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

2005-05-10

5

BPW 34 S (R18R)



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

Lötbedingungen
Soldering Conditions

BPW 34 S
BPW 34 S (R18R)

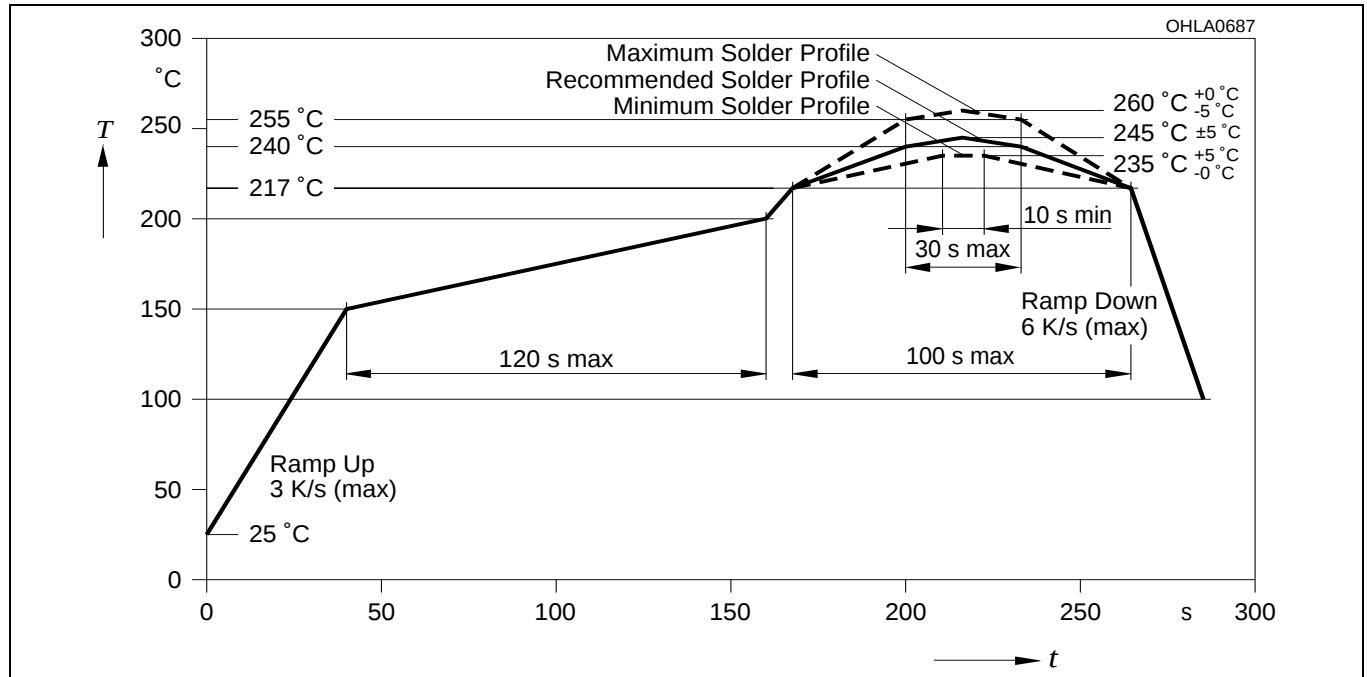
Vorbehandlung nach JEDEC Level 4
Preconditioning acc. to JEDEC Level 4

IR-Reflow Lötprofil für bleifreies Löt

(nach J-STD-020B)

IR Reflow Soldering Profile for lead free soldering

(acc. to J-STD-020B)

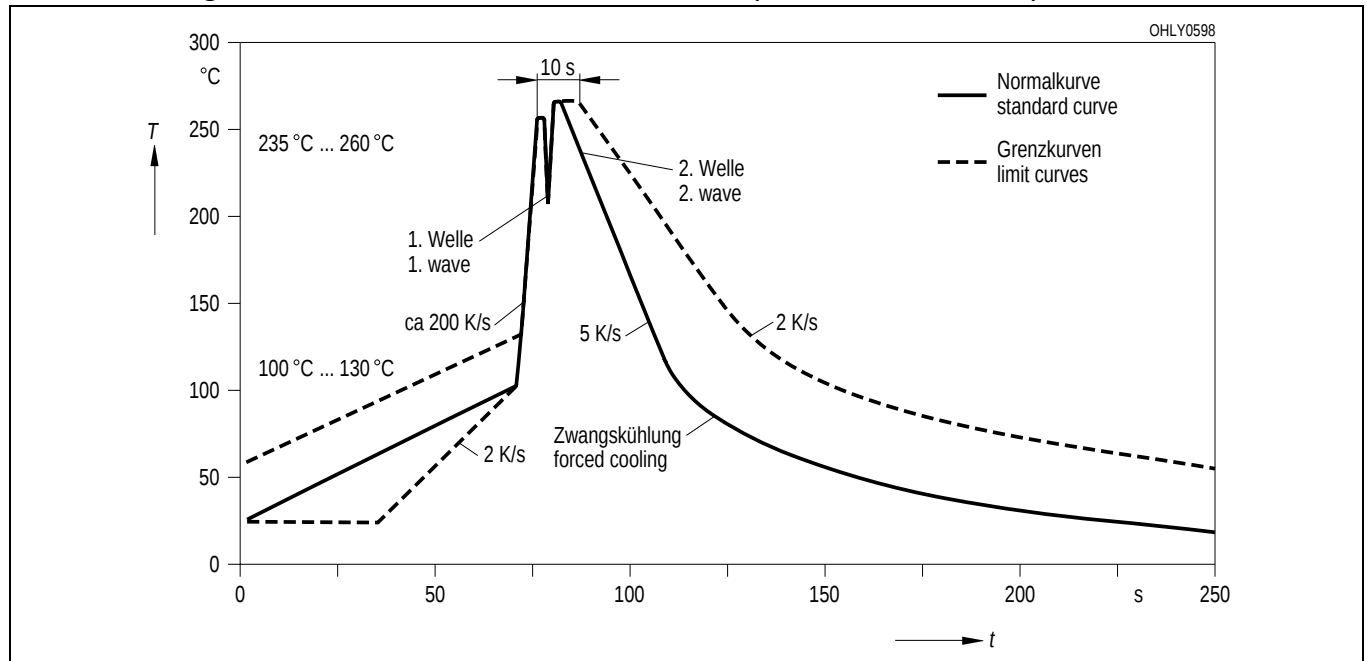


Wellenlöt (TTW)
TTW Soldering

BPW 34

(nach CECC 00802)

(acc. to CECC 00802)



Published by
OSRAM Opto Semiconductors GmbH
Wernerwerkstrasse 2, D-93049 Regensburg
www.osram-os.com

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Packing

Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

Components used in life-support devices or systems must be expressly authorized for such purpose! Critical components¹, may only be used in life-support devices or systems² with the express written approval of OSRAM OS.

¹ A critical component is a component used in a life-support device or system whose failure can reasonably be expected to cause the failure of that life-support device or system, or to affect its safety or effectiveness of that device or system.

² Life support devices or systems are intended (a) to be implanted in the human body, or (b) to support and/or maintain and sustain human life. If they fail, it is reasonable to assume that the health of the user may be endangered.